

In the Claims:

1.-20. (Cancelled)

21. (Currently Amended) A method of forming electrically connected contacting parts of a component integrated into a semiconductor substrate, the method comprising:

providing a first contact hole in an insulating layer; and

filling the contact hole with contact material so that the contact material is electrically connected to a line;

wherein a hard mask that is used to pattern probe the contact hole is also used to subsequently re-patterned to define structure the a conductor line trench which is connected thereto.

22. (New) The method of claim 21 wherein said hard mask is made from polycrystalline silicon.

23. (New) The method of claim 21 further comprising patterning said hard mask by means of a dry etching process.

24. (New) The method of claim 23 wherein said dry etching process comprises using at least one of the group SF<sub>6</sub>, HBr and He/O<sub>2</sub>.

25. (New) The method of claim 21 further comprising depositing a liner on a surface of said contact hole and line prior to said step of filling.

26. (New) The method of claim 25 wherein said liner is selected from the group consisting of Ti and TiN.

27. (New) The method of claim 21 wherein said step of filling the contact hole with contact material comprising filling said contact hole with tungsten.

28. (New) A method of forming a contact hole and a conductor trench connecting to said contact hole in an insulating layer using a common hard mask, the method comprising:  
providing said insulating layer;  
providing said hard mask patterned to form said contact hole;  
etching said contact hole in said insulating layer;  
re-patterning said hard mask to form said conductor trench connected to said contact hole;  
etching said conductor trench in said insulating layer; and  
filling said contact hole and said conductor trench with a conductive material such that said conductive material in said conductor trench and said contact hole are electrically connected.

29. (New) The method of claim 28 wherein said hard mask is made from polycrystalline silicon.

30. (New) The method of claim 28 further comprising covering said insulating layer with an ARC layer to fill said contact hole prior to said step of re-patterning said hard mask.

31. (New) The method of claim 28 wherein said step of repatterning said hard mask comprises etching said hard mask by means of a dry etching process.

32. (New) The method of claim 31 wherein said dry etching process comprises using at least one of the group SF<sub>6</sub>, HBr and He/O<sub>2</sub>.

33. (New) The method of claim 28 further comprising the step of depositing a liner on a surface of said contact hole and conductor trench prior to said step of filling.

34. (New) The method of claim 28 wherein said step of filling said contact hole with conductive material comprises filling said contact hole with tungsten.

35. (New) The method of claim 33 wherein said liner is selected from the group consisting of Ti and TiN.